查询"23 K38 A HI K A HI Transistor Silicon N-Channel MOS Type (MACH II π-MOS VI)

2SK3906

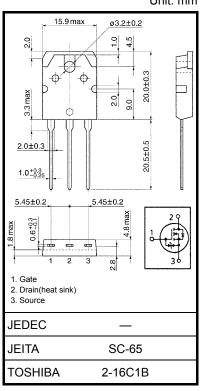
Switching Regulator Applications

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- Small gate charge: Qg = 60 nC (typ.)
- Fast reverse recovery time: t_{rr} = 400 ns (typ.) •
- Low drain-source ON-resistance: R_{DS} (ON) = 0.27 Ω (typ.)
- High forward transfer admittance: |Y_{fs}| = 15S (typ.)
- Low leakage current: I_{DSS} = 500 μA (V_{DS} = 600 V)
- Enhancement mode: $V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
Drain-source voltage			V _{DSS}	600	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)			V _{DGR}	600	V	
Gate-source voltage			V _{GSS}	±30	V	
Drain current	DC (No	te 1)	۱ _D	20	А	
	Pulse (No	te 1)	I _{DP}	80	~	
Drain power dissipation (Tc = 25° C)			PD	150	W	
Single-pulse avalanche energy (Note 2)			E _{AS}	792	mJ	
Avalanche current			I _{AR}	20	А	
Repetitive avalanche energy (Note 3)			E _{AR}	15	mJ	
Channel temperature			T _{ch}	150	°C	
Storage temperature range			T _{stg}	-55~150	°C	



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristic	Symbol	Мах	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	0.833	°C/W	
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$ (initial), L = 3.46 mH, I_{AR} = 20 A, R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm

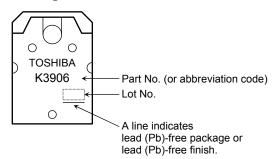
Eterrica Ponaracteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 25~V,~V_{DS}=0~V$		—	±10	μA
Gate-source breakdown voltage		V (BR) GSS	$I_D=\pm 10~\mu A,~V_{GS}=0~V$	±30	_		V
Drain cutoff current		I _{DSS}	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		_	500	μA
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	_		V
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0	_	4.0	V
Drain-source ON	rce ON-resistance $R_{DS(ON)}$ $V_{GS} = 10 V, I_D = 10 A$		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		0.27	0.33	Ω
Forward transfer	Forward transfer admittance		$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	7	15		S
Input capacitance		C _{iss}			4250		pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz$		10		
Output capacitance		C _{oss}			420		
Switching time	Rise time	tr	$V_{GS} = 10 V$ 0 V 0 V GS = 10 A 0 V 0 V		12		ns
	Turn-on time	t _{on}		_	45	_	
	Fall time	t _f			10		
	Turn-off time	t _{off}	$V_{DD}\simeq 200 \text{ V}$ Duty \leq 1%, t_{W} = 10 μs	_	80		
Total gate charge		Qg		_	60	_	
Gate-source charge		Q _{gs}	$V_{DD} \simeq 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	_	50	_	nC
Gate-drain charge		Q _{gd}]	_	10	_	

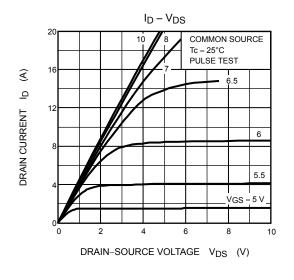
Source-Drain Ratings and Characteristics (Ta = 25°C)

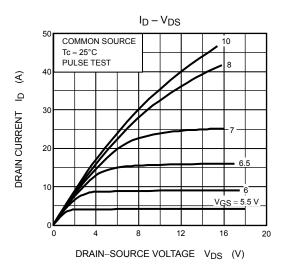
Characteristic	Symbol	Test Condition	Min	Тур.	Мах	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	20	А
Pulse drain reverse current (Note 1)	I _{DRP}	—			80	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 20 \text{ A}, \text{ V}_{GS} = 0 \text{ V},$	_	400	_	ns
Reverse recovery charge	Q _{rr}	dl _{DR} /dt = 100 A/µs		2.9	_	μC

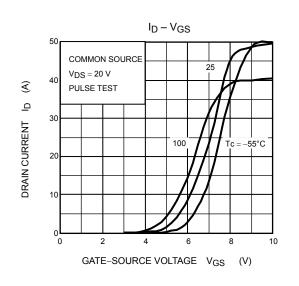
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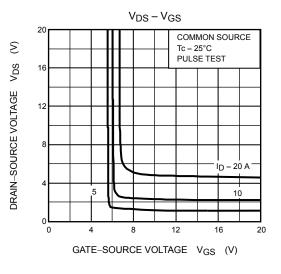


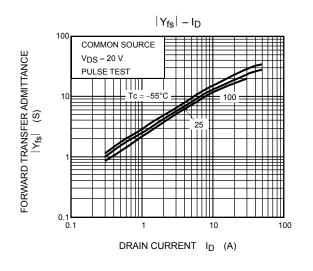
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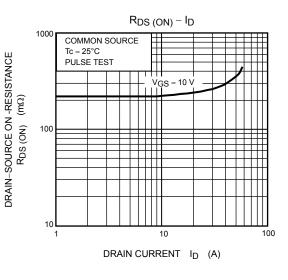




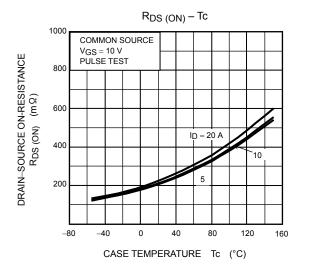


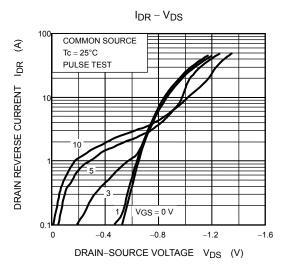


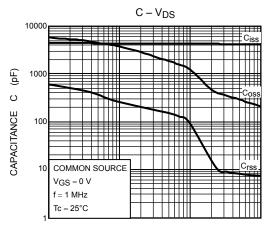




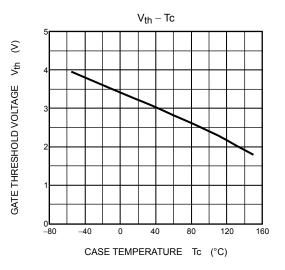
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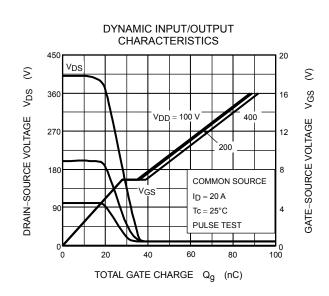


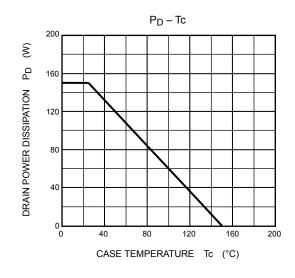




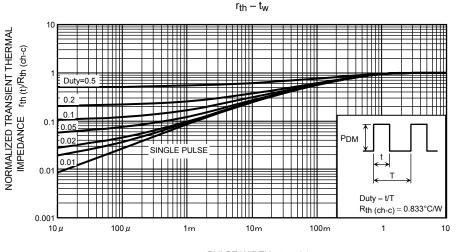
 $\label{eq:drain-source} \mathsf{DRAIN}-\mathsf{SOURCE}\;\;\mathsf{VOLTAGE}\;\;\;\mathsf{V}_{\mathsf{DS}}\;\;\;(\mathsf{V})$



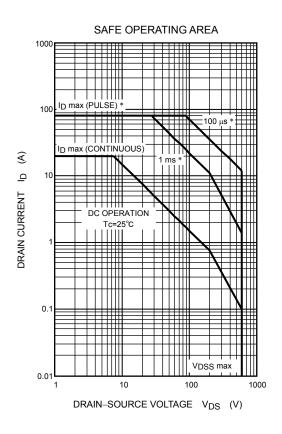


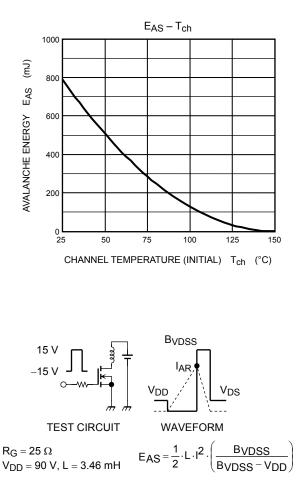


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PULSE WIDTH t_w (s)





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